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### Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

### Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-A7, ARM® Cortex®-M4
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Multimedia; NEON™ MPE
RAM Controllers	LPDDR2, LPDDR3, DDR3, DDR3L
Graphics Acceleration	No
Display & Interface Controllers	Keypad, LCD, MIPI
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (1), USB 2.0 OTG + PHY (2)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	0°C ~ 95°C (TJ)
Security Features	A-HAB, ARM TZ, CAAM, CSU, SJC, SNVS
Package / Case	541-LFBGA
Supplier Device Package	541-MAPBGA (19x19)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx7d7dvm10sc">https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx7d7dvm10sc</a>

- Advanced security—The processors deliver hardware-enabled security features that enable secure e-commerce, digital rights management (DRM), information encryption, secure boot, and secure software downloads. The security features are discussed in detail in the i.MX 7Dual security reference manual.
- Integrated power management—The processors integrate linear regulators and internally generate voltage levels for different power domains. This significantly simplifies system power management structure.

For a comprehensive list of the i.MX 7Dual features, see [Section 1.2, “Features.”](#)

## 1.1 Ordering information

[Table 1](#) provides examples of orderable sample part numbers covered by this data sheet.

**Table 1. Orderable parts**

Part Number	Options	Cortex-A7 CPU Speed Grade	Qualification Tier	Temperature ( $T_j$ )	Package
MCIMX7D7DVK10SD	EPDC, CAN 2 x Gigabit Ethernet 4 tamper pins 1 x ADC	1 GHz	Consumer <sup>1</sup>	0 to +95°C	12x12 mm 0.4 mm pitch BGA
MCIMX7D7DVM10SD	EPDC, CAN 2 x Gigabit Ethernet 10 tamper pins 2 x ADC	1 GHz	Consumer <sup>1</sup>	0 to +95°C	19x19 mm 0.75 mm pitch BGA
MCIMX7D5EVM10SD	No EPDC, CAN 2 x Gigabit Ethernet 10 tamper pins 2 x ADC	1 GHz	Industrial <sup>2</sup>	-20 to 105°C	19x19 mm 0.75 mm pitch BGA
MCIMX7D3DVK10SD	No EPDC, No CAN 2 x Gigabit Ethernet 4 tamper pins 1 x ADC	1 GHz	Consumer <sup>1</sup>	0 to +95°C	12x12 mm 0.4 mm pitch BGA
MCIMX7D3EVK10SD	No EPDC, No CAN 2 x Gigabit Ethernet 4 tamper pins 1 x ADC	1 GHz	Industrial <sup>2</sup>	-20 to +105°C	12x12 mm 0.4 mm pitch BGA
MCIMX7D2DVK12SD	No EPDC, No CAN 2 x Gigabit Ethernet 4 tamper pins 1 x ADC	1.2 GHz	Consumer	0 to 85°C	12x12 mm 0.4 mm pitch BGA
MCIMX7D2DVM12SD	No EPDC, No CAN 2 x Gigabit Ethernet 10 tamper pins 2 x ADC	1.2 GHz	Consumer	0 to 85°C	19x19mm 0.75 mm pitch BGA

<sup>1</sup> Consumer qualification grade assumes 5-year lifetime with 50% duty cycle.

<sup>2</sup> Industrial qualification grade assumes 10-year lifetime with 100% duty cycle.

## Electrical characteristics

The typical values shown in [Table 11](#) are required for use with NXP BSPs to ensure precise time keeping and USB operation. For RTC\_XTALI operation, two clock sources are available. If there is not an externally applied oscillator to RTC\_XTALI, the internal oscillator takes over.

- On-chip 32 kHz RC oscillator—this clock source has the following characteristics:
  - Approximately 25  $\mu$ A more  $I_{DD}$  than crystal oscillator
  - Approximately  $\pm 10\%$  tolerance
  - No external component required
  - Starts up faster than 32 kHz crystal oscillator
  - Three configurations for this input:
    - External oscillator
    - External crystal coupled to RTC\_XTALI and RTC\_XTALO
    - Internal oscillator

External crystal oscillator with on-chip support circuit:

- At power up, RC oscillator is utilized. After crystal oscillator is stable, the clock circuit switches over to the crystal oscillator automatically.
- Higher accuracy than RC oscillator
- If no external crystal is present, then the RC oscillator is utilized

The decision of choosing a clock source should be taken based on real-time clock use and precision timeout.

### 4.1.5 Maximum supply currents

The Power Virus numbers shown in [Table 12](#) represent a use case designed specifically to show the maximum current consumption possible. All cores are running at the defined maximum frequency and are limited to L1 cache accesses only to ensure no pipeline stalls. Although a valid condition, it would have a very limited practical use case, if at all, and be limited to an extremely low duty cycle unless the intention was to specifically show the worst case power consumption.

The MC3xPF3000xxxx, NXP's power management IC targeted for the i.MX 7Dual family of processors, supports the Power Virus mode operating at 1% duty cycle. Higher duty cycles are allowed, but a robust thermal design is required for the increased system power dissipation.

[Table 12](#) represents the maximum momentary current transients on power lines, and should be used for power supply selection. Maximum currents are higher by far than the average power consumption of typical use cases. For typical power consumption information, see the application note, [i.MX 7DS Power Consumption Measurement \(AN5383\)](#).

**Table 12. Maximum supply currents**

Power Rail	Source	Conditions	Max Current	Unit
VDD_ARM	From PMIC	—	500	mA
VDD_SOC	From PMIC	—	1000	mA

## Electrical characteristics

power saving. For example, the PMIC can change the DCDC rails to PFM mode to reduce the power consumption.

The power consumption in low power modes is defined in [Table 15](#).

**Table 15. Low Power Measurements**

Power rail	System IDLE			Low Power IDLE			SUSPEND			LPSR		
	Voltage	Current	Power	Voltage	Current	Power	Voltage	Current	Power	Voltage	Current	Power
	(V)	(mA)	(mW)	(V)	(mA)	(mW)	(V)	(mA)	(mW)	(V)	(mA)	(mW)
VDD_ARM	1.0	2.7	2.70	1.0	0.428	0.43	1.0	0.3	0.30	0.0	—	0.00
VDD_SOC	1.0	19.38	19.38	1.0	1.423	1.42	1.0	0.6	0.60	0.0	—	0.00
VDDA_1P8_IN	1.8	3.46	6.23	1.8	0.206	0.37	1.8	0.4	0.72	0.0	—	0.00
VDD_SNVS_IN	3.0	0.006	0.018	3.0	0.005	0.015	3.0	0.006	0.018	3.0	0.003	0.009
VDD_LPSR_IN	1.8	0.04	0.07	1.8	0.041	0.07	1.8	0.039	0.0702	1.8	0.04	0.07
NVCC_GPIO1/2	1.8	0.072	0.13	1.8	0.073	0.13	1.8	0.072	0.13	1.8	0.072	0.13
<b>Total</b>	—	—	<b>28.53</b>	—	—	<b>2.45</b>	—	—	<b>1.84</b>	—	—	<b>0.21</b>

All the power numbers defined in [Table 15](#) are based on typical silicon at 25°C.

### 4.1.7 USB PHY Suspend current consumption

#### 4.1.7.1 Low Power Suspend Mode

The VBUS Valid comparators and their associated bandgap circuits are enabled by default. [Table 16](#) shows the USB interface current consumption in Suspend mode with default settings.

**Table 16. USB PHY current consumption with default settings<sup>1</sup>**

Current	VDD_USB_OTG1_3P3_IN	VDD_USB_OTG2_3P3_IN
	790 uA	790 uA
1	Low Power Suspend is enabled by setting USBx_PORTSC1 [PHCD]=1 [Clock Disable (PLPSCD)].	

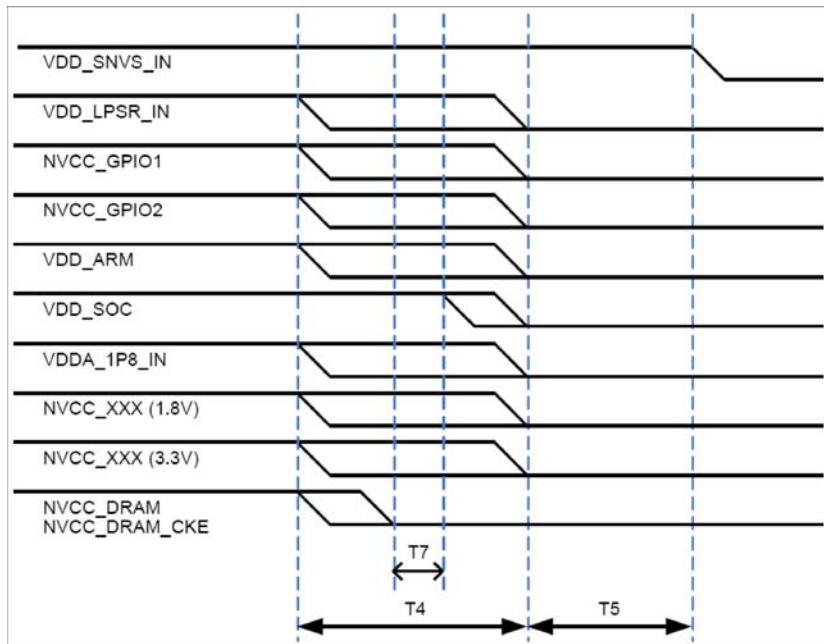


Figure 5. i.MX 7Dual power-down sequence

#### 4.1.11 Power supplies usage

I/O pins should not be externally driven while the I/O power supply for the pin (NVCC\_xxx) is OFF. This can cause internal latch-up and malfunctions due to reverse current flows. For information about I/O power supply of each pin, see “Power Rail” columns in pin list tables of [Section 6, “Package information and contact assignments.”](#)

## 4.2 Integrated LDO voltage regulator parameters

Various internal supplies can be powered from internal LDO voltage regulators. All the supply pins named \*\_CAP must be connected to external capacitors. The onboard LDOs are intended for internal use only and should not be used to power any external circuitry. See the *i.MX 7Dual Application Processor Reference Manual* (IMX7DRM) for details on the power tree scheme.

### NOTE

The \*\_CAP signals must not be powered externally. The \*\_CAP pins are for the bypass capacitor connection only.

## 4.2.1 Internal regulators

**Table 26. LDO parameters**

Parameter	Min	Max	Units
PVCC_GPIO_AT3P3_1P8	1.6	1.98	V
VDD_1P2	1.1	1.32	V
LPSR_1P0	0.95	1.155	V
VDDA_PHY_1P8	1.6	1.98	V
USB_OTG1_1P0	0.95	1.155	V

### 4.2.1.1 LDO\_1P2

The LDO\_1P2 regulator implements a programmable linear-regulator function from VDDA\_1P8\_IN (see [Table 9](#) for minimum and maximum input requirements). The typical output of the LDO, VDD\_1P2\_CAP, is 1.2 V. It is intended for use with the USB HSIC PHY, which uses this voltage level for its output driver. For additional information, see the “Power Management Unit (PMU)” chapter of the *i.MX 7Dual Application Processor Reference Manual* (IMX7DRM).

### 4.2.1.2 LDO\_1P0D

The LDO\_1P0D regulator implements a programmable linear-regulator function from VDDA\_1P8\_IN (see [Table 9](#) for minimum and maximum input requirements). The typical output of the LDO, VDD\_1P0D\_CAP, is 1.0 V. It is intended for use with the internal physical interfaces, including MIPI and PCIe PHY. For additional information, see the *i.MX 7Dual Application Processor Reference Manual* (IMX7DRM).

### 4.2.1.3 LDO\_1P0A

The LDO\_1P0A regulator implements a programmable linear-regulator function from VDDA\_1P8\_IN (see [Table 9](#) for minimum and maximum input requirements). The typical output of the LDO, VDD\_1P0A\_CAP, is 1.0 V. It is intended for use with the internal analog modules, including the XTAL, ADC, PLL, and Temperature Sensor. For additional information, see the *i.MX 7Dual Application Processor Reference Manual* (IMX7DRM).

### 4.2.1.4 LDO\_USB1\_1PO/LDO\_USB2\_1P0

The LDO\_USB1\_1PO/LDO\_USB2\_1P0 regulators implement a fixed linear-regulator function from VDD\_USB\_OTG1\_3P3\_IN and VDD\_USB\_OTG2\_3P3\_IN power inputs respectively (see [Table 9](#) for minimum and maximum input requirements). The typical output voltage is 1.0 V. It is intended for use with the internal USB physical interfaces (USB PHY1 and USB PHY2). For additional information, see the *i.MX 7Dual Application Processor Reference Manual* (IMX7DRM).

## Electrical characteristics

- General Purpose I/O (GPIO)
- Double Data Rate I/O (DDR) for LPDDR3 and DDR3 modes
- Differential I/O (CCM\_CLK1)

### 4.5.1 General purpose I/O (GPIO) DC parameters

[Table 29](#) shows DC parameters for GPIO pads. The parameters in [Table 29](#) are guaranteed per the operating ranges in [Table 9](#), unless otherwise noted.

**Table 29. GPIO DC Parameters**

Parameter	Symbol	Test Conditions	Min	Max	Units
High-level output voltage	$V_{OH}$	$I_{OH} = -1.8\text{mA}, -3.6\text{mA}, -7.2\text{mA}, -10.8\text{mA}$	$0.8 \times OVDD$	$OVDD$	V
Low-level output voltage	$V_{OL}$	$I_{OL} = 1.8\text{mA}, 3.6\text{mA}, 7.2\text{mA}, 10.8\text{mA}$	0	$0.2 \times OVDD$	V
High-level input voltage	$V_{IH}$	—	$0.7 \times OVDD$	$OVDD + 0.3$	V
Low-level input voltage	$V_{IL}$	—	-0.3	$0.3 \times OVDD$	V
Input hysteresis	$V_{HYS}$	—	0.15	—	V
Pull-up resistor (5_kΩ PU)	—	$V_{DD} = 1.8 \pm 0.15\text{ V}$	5.94	5.98	KΩ
Pull-up resistor (5_kΩ PU)	—	$V_{DD} = 3.3 \pm 0.3\text{ V}$	4.8	5.3	KΩ
Pull-up resistor (47_kΩ PU)	—	$V_{DD} = 1.8 \pm 0.15\text{ V}$	46.1	50.6	KΩ
Pull-up resistor (47_kΩ PU)	—	$V_{DD} = 3.3 \pm 0.3\text{ V}$	45.8	49.8	KΩ
Pull-up resistor (100_kΩ PU)	—	$V_{DD} = 1.8 \pm 0.15\text{ V}$	97.5	105.9	KΩ
Pull-up resistor (100_kΩ PU)	—	$V_{DD} = 3.3 \pm 0.3\text{ V}$	101	105	KΩ
Pull-down resistor (100_kΩ PU)	—	$V_{DD} = 1.8 \pm 0.15\text{ V}$	101	108.6	KΩ
Pull-down resistor (100_kΩ PD)	—	$V_{DD} = 3.3 \pm 0.3\text{ V}$	101	108	KΩ
Input current (no PU/PD)	$I_{OZ}$	—	-5	5	µA
Sink/source current in Push-Pull mode	—	Driving currents (@100MHz, $V_{OL/H} = 0.5 \times OVDD$ , SS, 125°C) $OVDD = 2.7\text{ V}$	-32.9	32.9	mA

### 4.5.2 DDR I/O DC electrical characteristics

The DDR I/O pads support DDR3/DDR3L, LPDDR2, and LPDDR3 operational modes. The DDR Memory Controller (DDRMC) is designed to be compatible with JEDEC-compliant SDRAMs. The DDRC supports the following memory types:

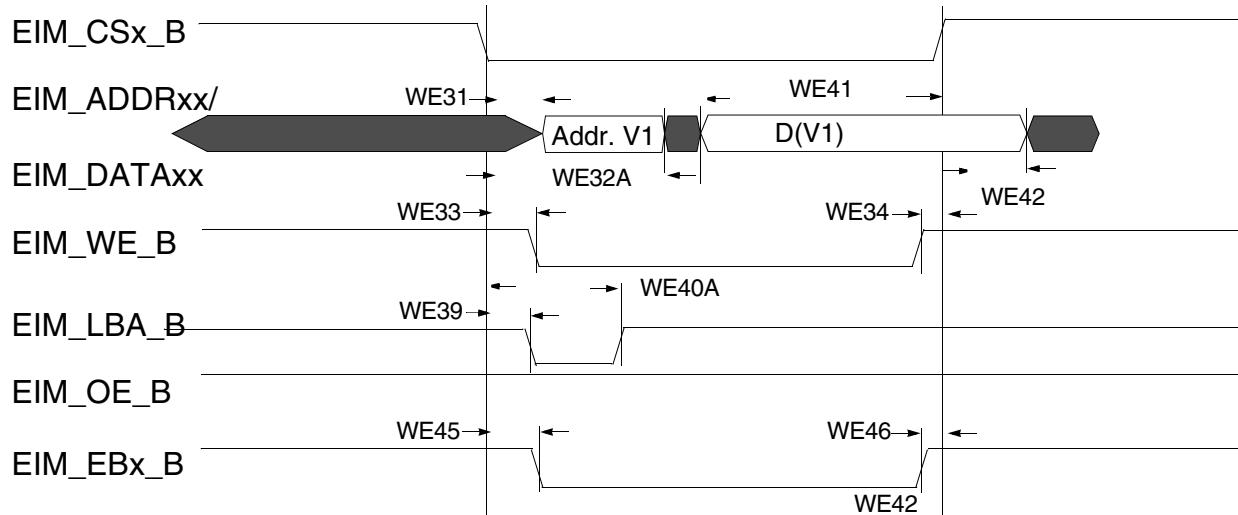
- DDR3 SDRAM compliant to JESD79-3E DDR3 JEDEC standard release July, 2010
- LPDDR2 SDRAM compliant to JESD209-2B LPDDR2 JEDEC standard release June, 2009
- LPDDR3 SDRAM compliant to JESD209-3B LPDDR3 JEDEC standard release August, 2013

### 4.8.3.3 Examples of EIM synchronous accesses

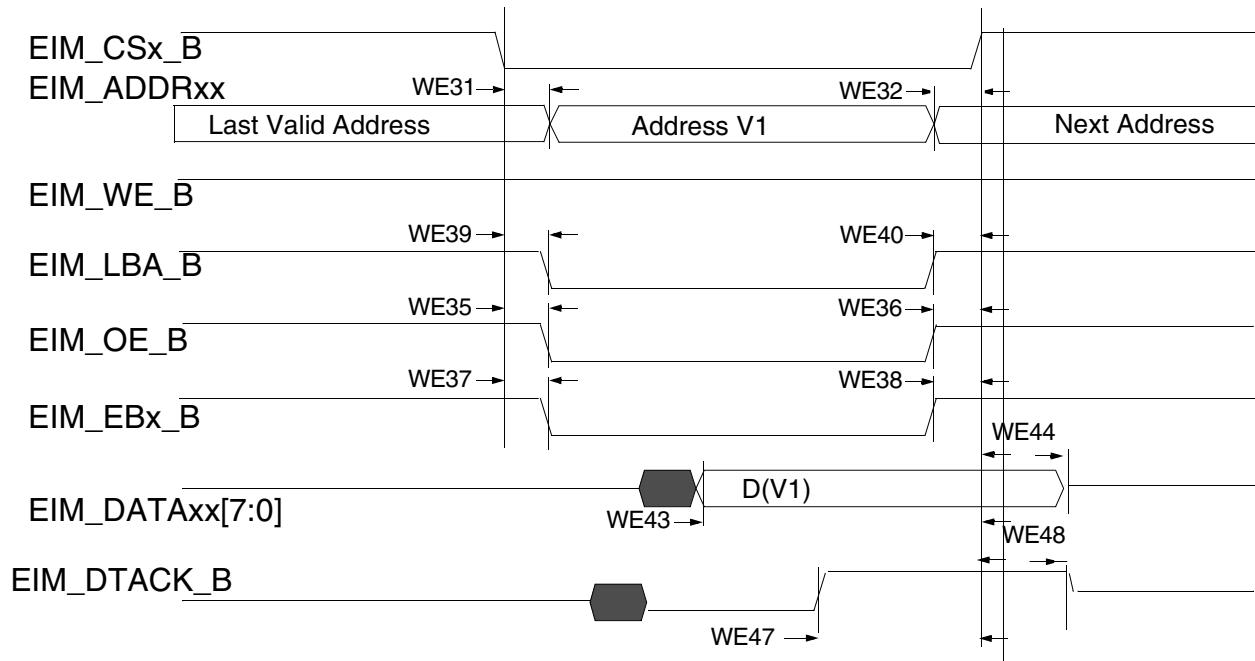
Table 45. EIM bus timing parameters<sup>1</sup>

ID	Parameter	BCD = 0		BCD = 1		BCD = 2		BCD = 3	
		Min	Max	Min	Max	Min	Max	Min	Max
WE1	EIM_BCLK Cycle time <sup>2</sup>	t	—	2 x t	—	3 x t	—	4 x t	—
WE2	EIM_BCLK Low Level Width	0.4 x t	—	0.8 x t	—	1.2 x t	—	1.6 x t	—
WE3	EIM_BCLK High Level Width	0.4 x t	—	0.8 x t	—	1.2 x t	—	1.6 x t	—
WE4	Clock rise to address valid <sup>3</sup>	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE5	Clock rise to address invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE6	Clock rise to EIM_CSx_B valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE7	Clock rise to EIM_CSx_B invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE8	Clock rise to EIM_WE_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE9	Clock rise to EIM_WE_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE10	Clock rise to EIM_OE_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE11	Clock rise to EIM_OE_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE12	Clock rise to EIM_EBx_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE13	Clock rise to EIM_EBx_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE14	Clock rise to EIM_LBA_B Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE15	Clock rise to EIM_LBA_B Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE16	Clock rise to Output Data Valid	-0.5 x t - 1.25	-0.5 x t + 1.75	-t - 1.25	-t + 1.75	-1.5 x t - 1.25	-1.5 x t + 1.75	-2 x t - 1.25	-2 x t + 1.75
WE17	Clock rise to Output Data Invalid	0.5 x t - 1.25	0.5 x t + 1.75	t - 1.25	t + 1.75	1.5 x t - 1.25	1.5 x t + 1.75	2 x t - 1.25	2 x t + 1.75
WE18	Input Data setup time to Clock rise	2	—	4	—	—	—	—	—
WE19	Input Data hold time from Clock rise	2	—	2	—	—	—	—	—
WE20	EIM_WAIT_B setup time to Clock rise	2	—	4	—	—	—	—	—
WE21	EIM_WAIT_B hold time from Clock rise	2	—	2	—	—	—	—	—

## Electrical characteristics

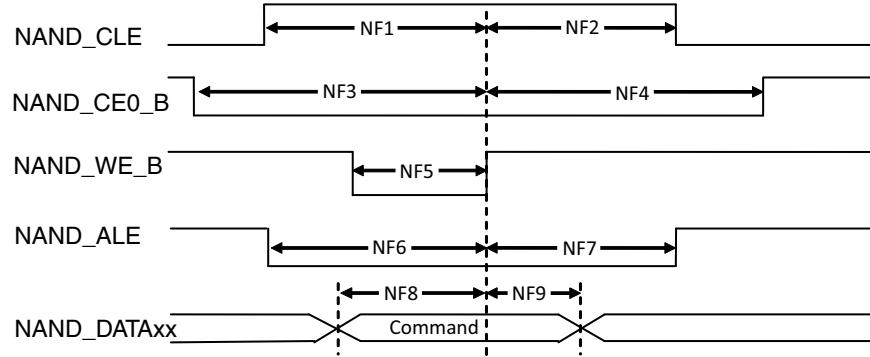


**Figure 21. Asynchronous A/D muxed write access**

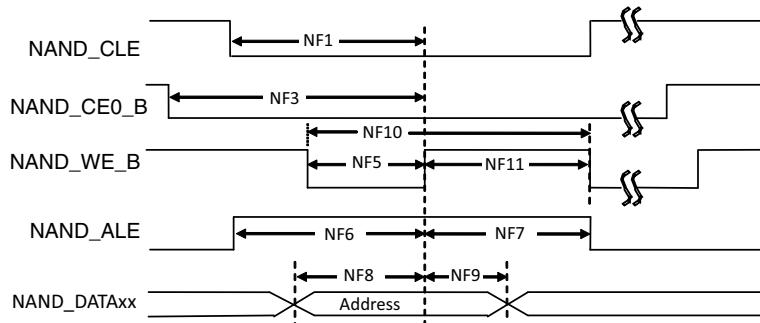


**Figure 22. DTACK mode read access (DAP=0)**

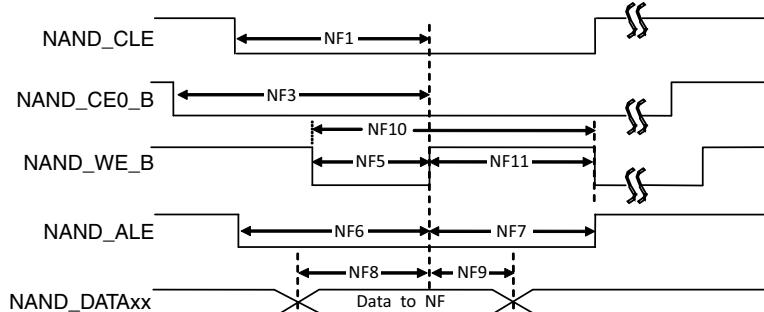
## Electrical characteristics



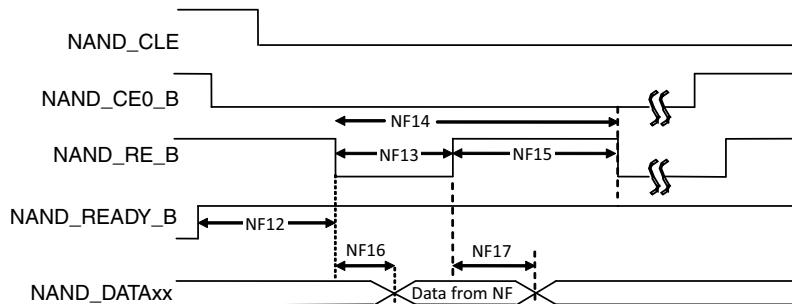
**Figure 33. Command Latch cycle timing diagram**



**Figure 34. Address Latch cycle timing diagram**



**Figure 35. Write Data Latch cycle timing diagram**



**Figure 36. Read Data Latch cycle timing diagram (Non-EDO Mode)**

**Table 61. SD/eMMC4.3 interface timing specification(continued)**

ID	Parameter	Symbols	Min	Max	Unit
<b>uSDHC Input/Card Outputs SD_CMD, SDx_DATAx (Reference to CLK)</b>					
SD7	uSDHC Input Setup Time	$t_{ISU}$	2.5	—	ns
SD8	uSDHC Input Hold Time <sup>4</sup>	$t_{IH}$	1.5	—	ns

<sup>1</sup> In Low-Speed mode, card clock must be lower than 400 kHz, voltage ranges from 2.7 to 3.6 V.

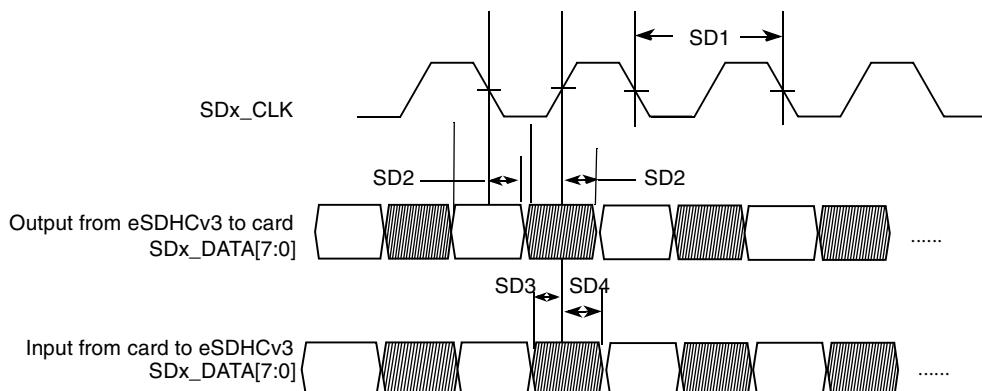
<sup>2</sup> In Normal (Full) -Speed mode for SD/SDIO card, clock frequency can be any value between 0—25 MHz. In High-speed mode, clock frequency can be any value between 0—50 MHz.

<sup>3</sup> In Normal (Full) -Speed mode for MMC card, clock frequency can be any value between 0—20 MHz. In High-speed mode, clock frequency can be any value between 0—52 MHz.

<sup>4</sup> To satisfy hold timing, the delay difference between clock input and cmd/data input must not exceed 2 ns.

#### 4.10.2.2 eMMC4.4/4.41 (dual data rate) AC timing

Figure 47 depicts the timing of eMMC4.4/4.41. Table 62 lists the eMMC4.4/4.41 timing characteristics. Be aware that only DATA is sampled on both edges of the clock (not applicable to CMD).

**Figure 47. eMMC4.4/4.41 timing****Table 62. eMMC4.4/4.41 interface timing specification**

ID	Parameter	Symbols	Min	Max	Unit
<b>Card Input Clock</b>					
SD1	Clock Frequency (eMMC4.4/4.41 DDR)	$f_{PP}$	0	52	MHz
SD1	Clock Frequency (SD3.0 DDR)	$f_{PP}$	0	50	MHz
<b>uSDHC Output / Card Inputs SD_CMD, SDx_DATAx (Reference to CLK)</b>					
SD2	uSDHC Output Delay	$t_{OD}$	2.7	6.9	ns
<b>uSDHC Input / Card Outputs SD_CMD, SDx_DATAx (Reference to CLK)</b>					

#### 4.10.3.1.3 MII asynchronous inputs signal timing (ENET\_CRS and ENET\_COL)

Figure 53 shows MII asynchronous input timings. Table 68 describes the timing parameter (M9) shown in the figure.

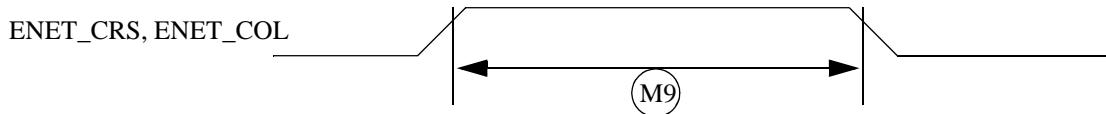


Figure 53. MII async inputs timing diagram

Table 68. MII asynchronous inputs signal timing

ID	Characteristic	Min.	Max.	Unit
M9 <sup>1</sup>	ENET_CRS to ENET_COL minimum pulse width	1.5	—	ENET_TX_CLK period

<sup>1</sup> ENET\_COL has the same timing in 10-Mbit 7-wire interface mode.

#### 4.10.3.1.4 MII Serial management channel timing (ENET\_MDIO and ENET\_MDC)

The MDC frequency is designed to be equal to or less than 2.5 MHz to be compatible with the IEEE 802.3 MII specification. However the ENET can function correctly with a maximum MDC frequency of 15 MHz.

Figure 54 shows MII asynchronous input timings. Table 69 describes the timing parameters (M10–M15) shown in the figure.

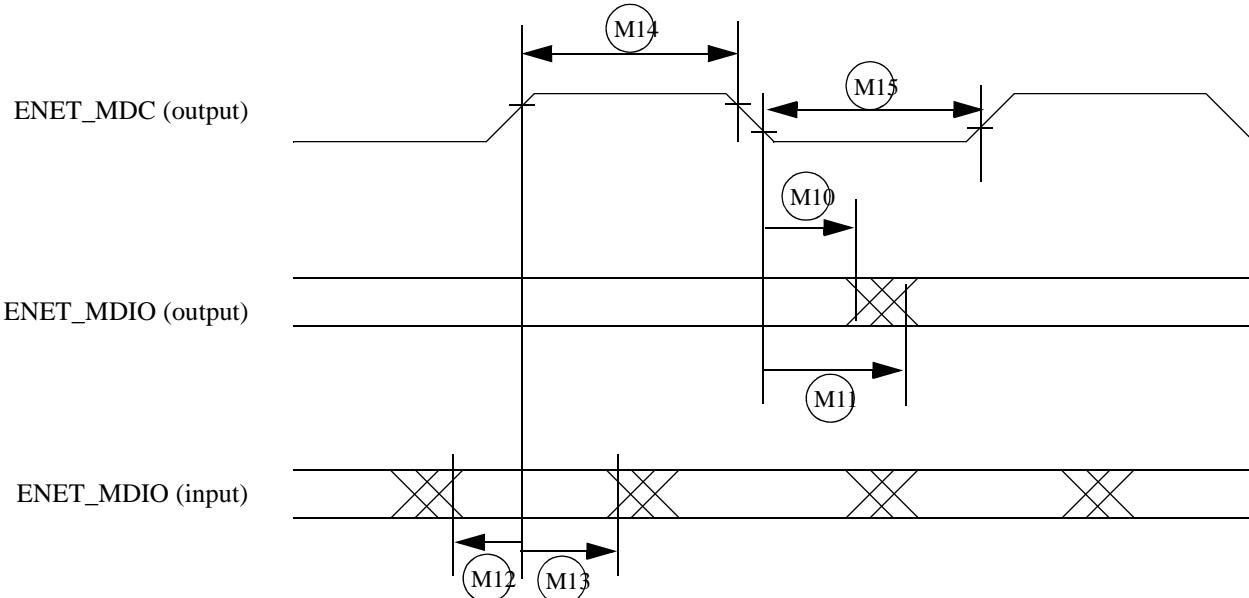


Figure 54. MII serial management channel timing diagram

**Table 70. RMII signal timing**

ID	Characteristic	Min.	Max.	Unit
M16	ENET_CLK pulse width high	35%	65%	ENET_CLK period
M17	ENET_CLK pulse width low	35%	65%	ENET_CLK period
M18	ENET_CLK to ENET0_RXD[1:0], ENET_TX_DATA invalid	4	—	ns
M19	ENET_CLK to ENET0_RXD[1:0], ENET_TX_DATA valid	—	15	ns
M20	ENET_RX_DATAD[1:0], ENET_RX_EN(ENET_RX_EN), ENET_RX_ER to ENET_CLK setup	4	—	ns
M21	ENET_CLK to ENET_RX_DATAD[1:0], ENET_RX_EN, ENET_RX_ER hold	2	—	ns

#### 4.10.3.3 Signal switching specifications

The following timing specifications meet the requirements for RGMII interfaces for a range of transceiver devices.

**Table 71. RGMII signal switching specifications<sup>1</sup>**

Symbol	Description	Min.	Max.	Unit
T <sub>cyc</sub> <sup>2</sup>	Clock cycle duration	7.2	8.8	ns
T <sub>skewT</sub> <sup>3</sup>	Data to clock output skew at transmitter	-500	500	ps
T <sub>skewR</sub> <sup>3</sup>	Data to clock input skew at receiver	1	2.6	ns
Duty_G <sup>4</sup>	Duty cycle for Gigabit	45	55	%
Duty_T <sup>4</sup>	Duty cycle for 10/100T	40	60	%
Tr/Tf	Rise/fall time (20–80%)	—	0.75	ns

<sup>1</sup> The timings assume the following configuration:

DDR\_SEL = (11)b

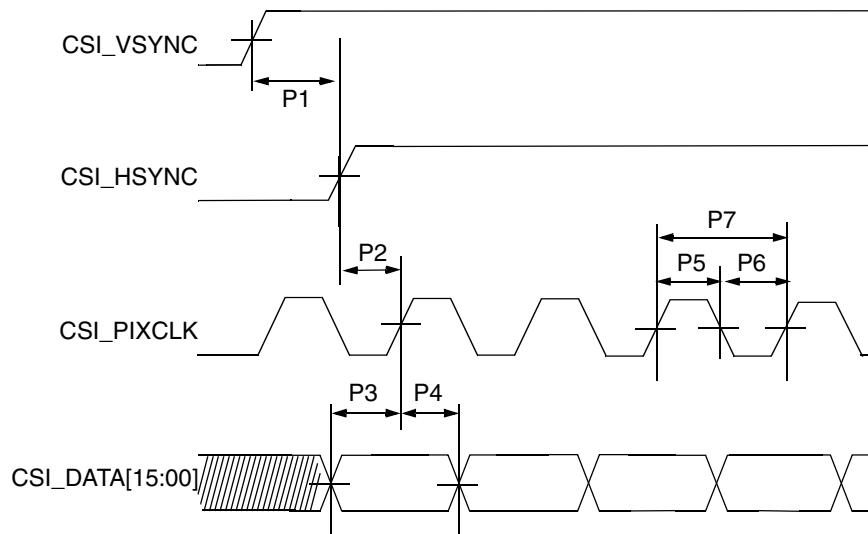
DSE (drive-strength) = (111)b

<sup>2</sup> For 10 Mbps and 100 Mbps, T<sub>cyc</sub> will scale to 400 ns ±40 ns and 40 ns ±4 ns respectively.

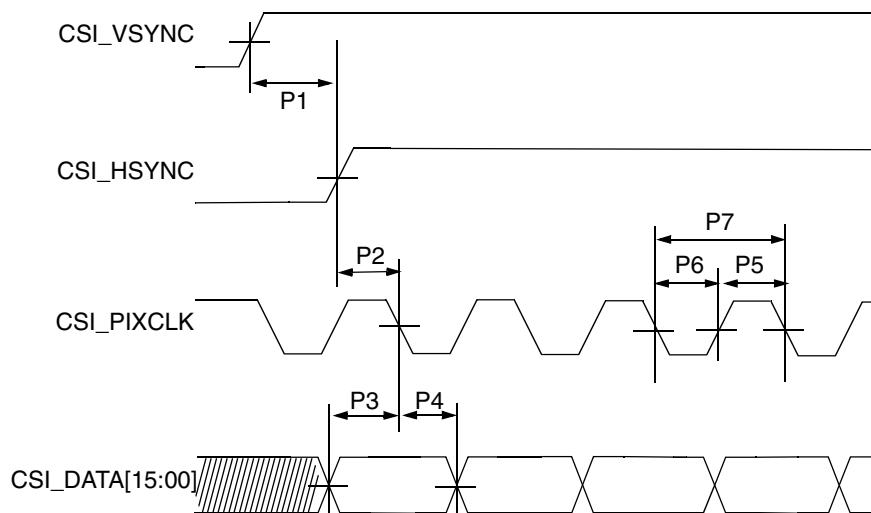
<sup>3</sup> For all versions of RGMII prior to 2.0; This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns and less than 2.0 ns will be added to the associated clock signal. For 10/100, the Max value is unspecified.

<sup>4</sup> Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domain as long as minimum duty cycle is not violated and stretching occurs for no more than three Tcyc of the lowest speed transitioned between.

(VSYNC), then CSI\_HSYNC (HSYNC) is asserted and holds for the entire line. The pixel clock, CSI\_PIXCLK (PIXCLK), is valid as long as HSYNC is asserted.



**Figure 61. CSI Gated Clock Mode—Sensor Data at Falling Edge, Latch Data at Rising Edge**



**Figure 62. CSI Gated Clock Mode—Sensor Data at Rising Edge, Latch Data at Falling Edge**

**Table 74. CSI Gated Clock Mode Timing Parameters**

ID	Parameter	Symbol	Min.	Max.	Units
P1	CSI_VSYNC to CSI_HSYNC time	tV2H	33.5	—	ns
P2	CSI_HSYNC setup time	tHsu	1	—	ns
P3	CSI DATA setup time	tDsu	1	—	ns

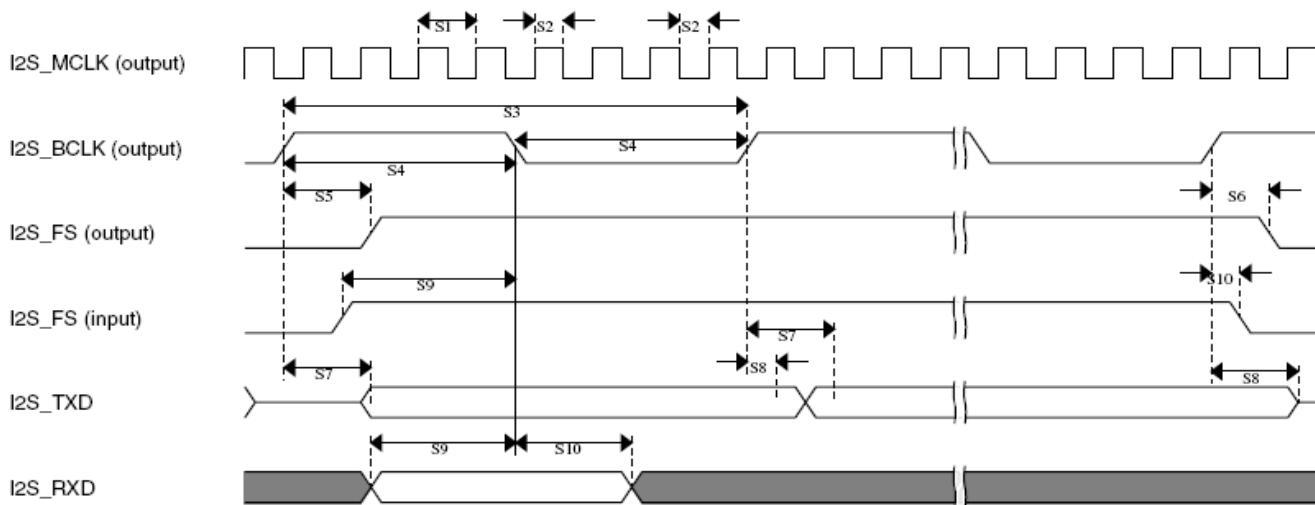
Table 77. Electrical and Timing Information(continued)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
<b>LP Line Drivers AC Specifications</b>						
$t_{rlp}, t_{flp}$	Single ended output rise/fall time	15% to 85%, $C_L < 70 \text{ pF}$	—	—	25	ns
$t_{reo}$		30% to 85%, $C_L < 70 \text{ pF}$	—	—	35	ns
$\delta V/\delta t_{SR}$	Signal slew rate	15% to 85%, $C_L < 70 \text{ pF}$	—	—	120	mV/ns
$C_L$	Load capacitance	—	0	—	70	pF
<b>HS Line Receiver AC Specifications</b>						
$t_{SETUP[RX]}$	Data to Clock Receiver Setup time	—	0.15	—	—	UI
$t_{HOLD[RX]}$	Clock to Data Receiver Hold time	—	0.15	—	—	UI
$\Delta V_{CMRX(HF)}$	Common mode interference beyond 450 MHz	—	—	—	200	mVpp
$\Delta V_{CMRX(LF)}$	Common mode interference between 50 MHz and 450 MHz.	—	-50	—	50	mVpp
$C_{CM}$	Common mode termination	—	—	—	60	pF
<b>LP Line Receiver AC Specifications</b>						
$e_{SPIKE}$	Input pulse rejection	—	—	—	300	Vps
$T_{MIN}$	Minimum pulse response	—	50	—	—	ns
$V_{INT}$	Pk-to-Pk interference voltage	—	—	—	400	mV
$f_{INT}$	Interference frequency	—	450	—	—	MHz
<b>Model Parameters used for Driver Load switching performance evaluation</b>						
$C_{PAD}$	Equivalent Single ended I/O PAD capacitance.	—	—	—	1	pF
$C_{PIN}$	Equivalent Single ended Package + PCB capacitance.	—	—	—	2	pF
$L_S$	Equivalent wire bond series inductance	—	—	—	1.5	nH
$R_S$	Equivalent wire bond series resistance	—	—	—	0.15	$\Omega$
$R_L$	Load resistance	—	80	100	125	$\Omega$

## Electrical characteristics

**Table 85. Master mode SAI timing(continued)**

Num	Characteristic	Min	Max	Unit
S5	SAI_BCLK to SAI_FS output valid	—	15	ns
S6	SAI_BCLK to SAI_FS output invalid	0	—	ns
S7	SAI_BCLK to SAI_TXD valid	—	15	ns
S8	SAI_BCLK to SAI_TXD invalid	0	—	ns
S9	SAI_RXD/SAI_FS input setup before SAI_BCLK	15	—	ns
S10	SAI_RXD/SAI_FS input hold after SAI_BCLK	0	—	ns



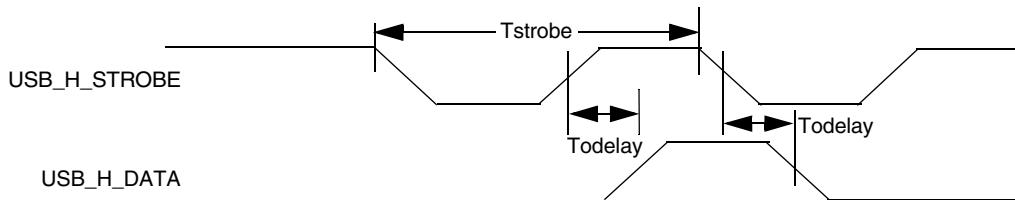
**Figure 77. SAI timing — master modes**

**Table 86. Master mode SAI timing**

Num	Characteristic	Min	Max	Unit
S11	SAI_BCLK cycle time (input)	40	—	ns
S12	SAI_BCLK pulse width high/low (input)	40%	60%	BCLK period
S13	SAI_FS input setup before SAI_BCLK	10	—	ns
S14	SAI_FA input hold after SAI_BCLK	2	—	ns
S15	SAI_BCLK to SAI_TXD/SAI_FS output valid	—	20	ns
S16	SAI_BCLK to SAI_TXD/SAI_FS output invalid	0	—	ns
S17	SAI_RXD setup before SAI_BCLK	10	—	ns
S18	SAI_RXD hold after SAI_BCLK	2	—	ns

**NOTE**

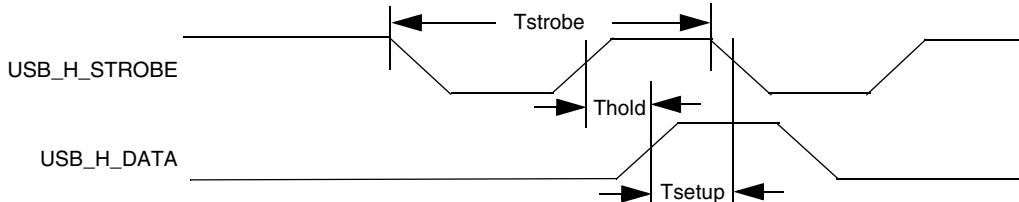
HSIC is DDR signal, following timing spec is for both rising and falling edge.

**4.10.15.1 Transmit timing**

**Figure 85. USB HSIC transmit waveform**

**Table 91. USB HSIC transmit parameters**

Name	Parameter	Min	Max	Unit	Comment
Tstrobe	strobe period	4.165	4.169	ns	
Todelay	data output delay time	550	1350	ps	Measured at 50% point
Tslew	strobe/data rising/falling time	0.7	2	V/ns	Averaged from 30% – 70% points

**4.10.15.2 Receive timing**

**Figure 86. USB HSIC receive waveform**

**Table 92. USB HSIC receive parameters<sup>1</sup>**

Name	Parameter	Min	Max	Unit	Comment
Tstrobe	strobe period	4.165	4.169	ns	
Thold	data hold time	300		ps	Measured at 50% point
Tsetup	data setup time	365		ps	Measured at 50% point
Tslew	strobe/data rising/falling time	0.7	2	V/ns	Averaged from 30% – 70% points

<sup>1</sup> The timings in the table are guaranteed when:  
—AC I/O voltage is between 0.9x to 1x of the I/O supply  
—DDR\_SEL configuration bits of the I/O are set to (10)b

## 6 Package information and contact assignments

This section includes the contact assignment information and mechanical package drawing.

### 6.1 12 x 12 mm package information

#### 6.1.1 Case 1997-01, 12 x 12, 0.4 mm pitch, ball matrix

The following figure shows the top, bottom, and side views of the 12×12 mm BGA package.

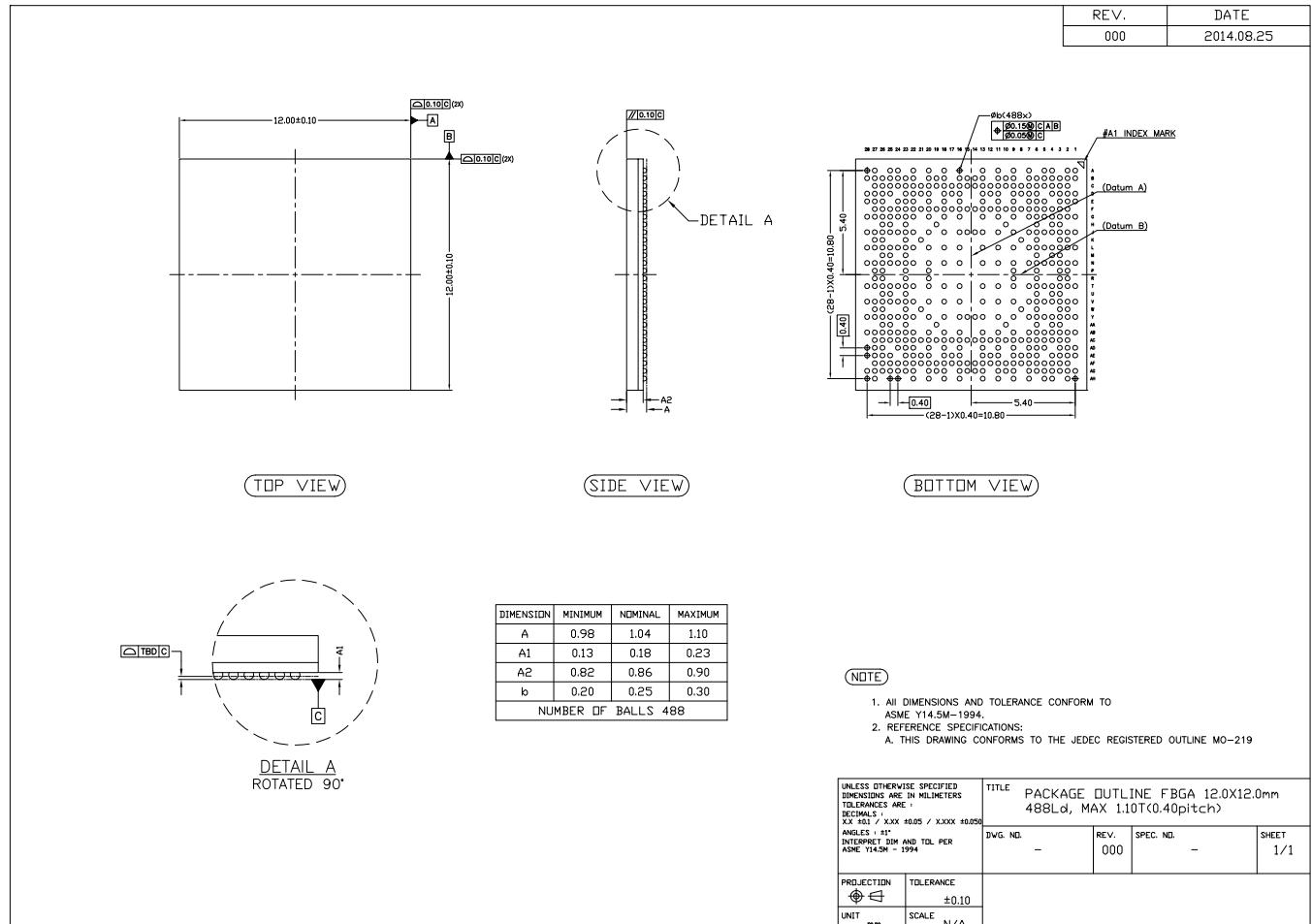


Figure 87. 12 x 12 mm BGA, Case x Package Top, Bottom, and Side Views

**Table 99. i.MX 7Dual 12 x 12 mm functional contact assignments(continued)**

Ball	Ball Name	Power Group	Ball type <sup>1</sup>	Default Mode <sup>1</sup>	Default Function <sup>1</sup>	PD/PD
P27	EPDC_D06	NVCC_EPDC1		ALT5	GPIO2_IO[6]	100K PD
N28	EPDC_D07	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[7]	100K PD
N27	EPDC_D08	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[8]	100K PD
N26	EPDC_D09	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[9]	100K PD
N25	EPDC_D10	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[10]	100K PD
N24	EPDC_D11	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[11]	100K PD
M26	EPDC_D12	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[12]	100K PD
L26	EPDC_D13	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[13]	100K PD
L25	EPDC_D14	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[14]	100K PD
N22	EPDC_D15	NVCC_EPDC1	GPIO	ALT5	GPIO2_IO[15]	100K PD
J23	EPDC_GDCLK	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[24]	100K PD
J22	EPDC_GDOE	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[25]	100K PD
L24	EPDC_GDRL	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[26]	100K PD
K27	EPDC_GDSP	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[27]	100K PD
J27	EPDC_PWRCOM	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[30]	100K PD
J26	EPDC_PWRSTAT	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[31]	100K PD
J25	EPDC_SDCE0	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[20]	100K PD
J24	EPDC_SDCE1	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[21]	100K PD
G22	EPDC_SDCE2	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[22]	100K PD
G23	EPDC_SDCE3	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[23]	100K PD
G24	EPDC_SDCLK	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[16]	100K PD
J28	EPDC_SDLE	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[17]	100K PD
G25	EPDC_SDOE	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[18]	100K PD
F26	EPDC_SDSHR	NVCC_EPDC2	GPIO	ALT5	GPIO2_IO[19]	100K PD
AF02	GPANAIO	VDDA_1P8	GPIO		GPANAIO	
V04	GPIO1_IO00	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO00	100K PU
V05	GPIO1_IO01	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO01	100K PD
Y07	GPIO1_IO02	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO02	100K PD
Y06	GPIO1_IO03	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO03	100K PD
Y05	GPIO1_IO04	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO04	100K PD
Y04	GPIO1_IO05	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO05	100K PD
V06	GPIO1_IO06	NVCC_GPIO1	GPIO	ALT0	GPIO1_IO06	100K PD

## Package information and contact assignments

**Table 100. i.MX 7Dual 12 x 12 mm 0.4 mm pitch ball map(continued)**

U	T	R	P	Z	M	L	K	J	H
1	UART1_RXD		ECSP12_SCLK		VDD_SOC		SD3_STROBE		1
2	UART2_RXD	ECSP12_SS0	ECSP12_MISO	ECSP12_MOSI	VDD_SOC	ECSP11_SCLK	SD3_RESET_B		2
3	UART3_TXD	UART2_TXD	VDD_SOC	ECSP11_SS0	ECSP11_MISO	ECSP11_MOSI	VDD_SOC	SD2_RESET_B	3
4	VSS	I2C4_SDA		I2C1_SCL	VSS	SD3_CMD	SD3_DATA7	VSS	
5		I2C4_SCL		I2C1_SDA		SD3_DATA4	SD3_DATA6		5
6	VSS	I2C3_SCL	VDD_SOC	I2C2_SCL	VSS	SD3_DATA3	VDD_SOC	SD3_CLK	
7		I2C3_SDA		I2C2_SDA		SD3_DATA2	SD3_DATA5		6
8					VDD_SOC				7
9	NVCC_UART	NVCC_I2C	NVCC_SPI	NVCC_SD3	NVCC_SD2		VDD_SOC		8
10							VDD_SOC		9
11	VSS			VSS	VDD_SOC		NVCC_SD1		10
12									11
13				VDD_SOC	VDD_SOC	VSS	NVCC_SAI		12
14							PVCC_SAI_SD_CAP		13
15							VDDA_MIP1P8		14
16				VDD_SOC	VDD_SOC	VSS	VDD_MIP1P0		15
17									16
18				VSS	VDD_SOC		NVCC_ENET1		17
19							VDD_ARM		18
20	DRAM_VREF	PVCC_EPDC_LCD_CAP	NVCC_EPDC1	NVCC_EPDC2	NVCC_LCD		VDD_ARM		19
21							VDD_ARM		20
22	DRAM_DATA27			EPDC1_DATA15	EPDC1_BDR1		EPDC1_GDOE		21
23	VSS	DRAM_DATA26	VDD_SOC	EPDC1_DATA04	VSS	EPDC1_BDRO	VDD_ARM	EPDC1_GDCLK	22
24	DRAM_DATA31			EPDC1_DATA11	EPDC1_GDRL		EPDC1_SDCE1		23
25	VSS	DRAM_DATA30		EPDC1_DATA10	VSS	EPDC1_DATA14	EPDC1_SDCE0	VSS	24
26	EPDC1_DATA01	EPDC1_DATA02	VDD_SOC	EPDC1_DATA09	EPDC1_DATA12	EPDC1_DATA13	VDD_ARM	EPDC1_PWRSTAT	25
27	EPDC1_DATA00	EPDC1_DATA03	EPDC1_DATA06	EPDC1_DATA08	VDD_ARM	EPDC1_GDSP	EPDC1_PWRCOM		26
28	EPDC1_DATA05			EPDC1_DATA07	VDD_ARM		EPDC1_SDLE		27
	U	T	R	P	Z	M	L	K	28

## Package information and contact assignments

**Table 100. i.MX 7Dual 12 x 12 mm 0.4 mm pitch ball map(continued)**

	AH	AG	AF	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	
		VSS	XTAL_O																													
1	2	VDD_XTAL_1P8	XTAL_I																													
2	3	VDDA_ADC1_1P8	VDDA_1P8_IN																													
3	4	VDDA_TEMPSENSOR_1P8	VDD_LPSSR_IN																													
4	5	VDDA_TEMPSENSOR_1P8	VDD_LPSSR_1P0_CAP	TEMPSENSOR_RESERVED																												
5	6	VDDA_1P0_CAP	VDD_SNVS_1P8_CAP	TEMPSENSOR_RESERVED	REXT																											
6	7	RTC_XTAL_O	RTC_XTAL_I																													
7	8	VSS	VSS																													
8	9	VSS	VSS																													
9	10	PCIE_REFCLKOUT_P	PCIE_REFCLKOUT_N																													
10	11	PCIE_REFCLKOUT_P	PCIE_REFCLKIN_N																													
11	12	PCIE_REFCLKIN_P	PCIE_REFCLKIN_N																													
12	13	PCIE_RX_P	PCIE_RX_N																													
13	14	PCIE_TX_P	PCIE_TX_N																													
14	15	PCIE_RX_P	PCIE_RX_N																													
15	16	PCIE_TX_P	PCIE_TX_N																													
16	17	NVCC_DRAM	NVCC_DRAM																													
17	18	NVCC_DRAM	NVCC_DRAM																													
18	19	DRAM_DATA01	DRAM_DATA01																													
19	20	DRAM_DATA02	DRAM_DATA02																													
20	21	DRAM_DATA04	DRAM_DATA04																													
21	22	DRAM_DATA05	DRAM_DATA05																													
22	23	DRAM_SDQS0_N	DRAM_SDQS0_N																													
23	24	DRAM_DQMO	DRAM_SDQS0_P																													
24	25	DRAM_RAS_B	DRAM_CAS_B																													
25	26	DRAM_SDWE_B	DRAM_ADDR11																													
26	27	VSS	DRAM_ADDR13																													
27	28	AH	AG																													